

ABSTRACT

A nonvolatile semiconductor storage element, which is provided with a floating gate electrode, and a dielectric capacitor and a ferroelectric capacitor both connected to the floating gate electrode. By applying voltage between a first polarization voltage supplying terminal and a second polarization voltage supplying terminal, polarization serving as information is generated in the ferroelectric film of the ferroelectric capacitor. Additionally, when a read-out voltage is applied between the ground terminal and the power source voltage terminal that are in connection with the source and drain regions, the MISFET is turned either on or off in correspondence to the state of the charge held in the floating gate electrode, and thus information within the floating gate electrode is read out.